

1 550 nm OPTICAL FIBER COMMUNICATIONS  
 InGaAsP MQW-DFB LASER DIODE COAXIAL MODULE

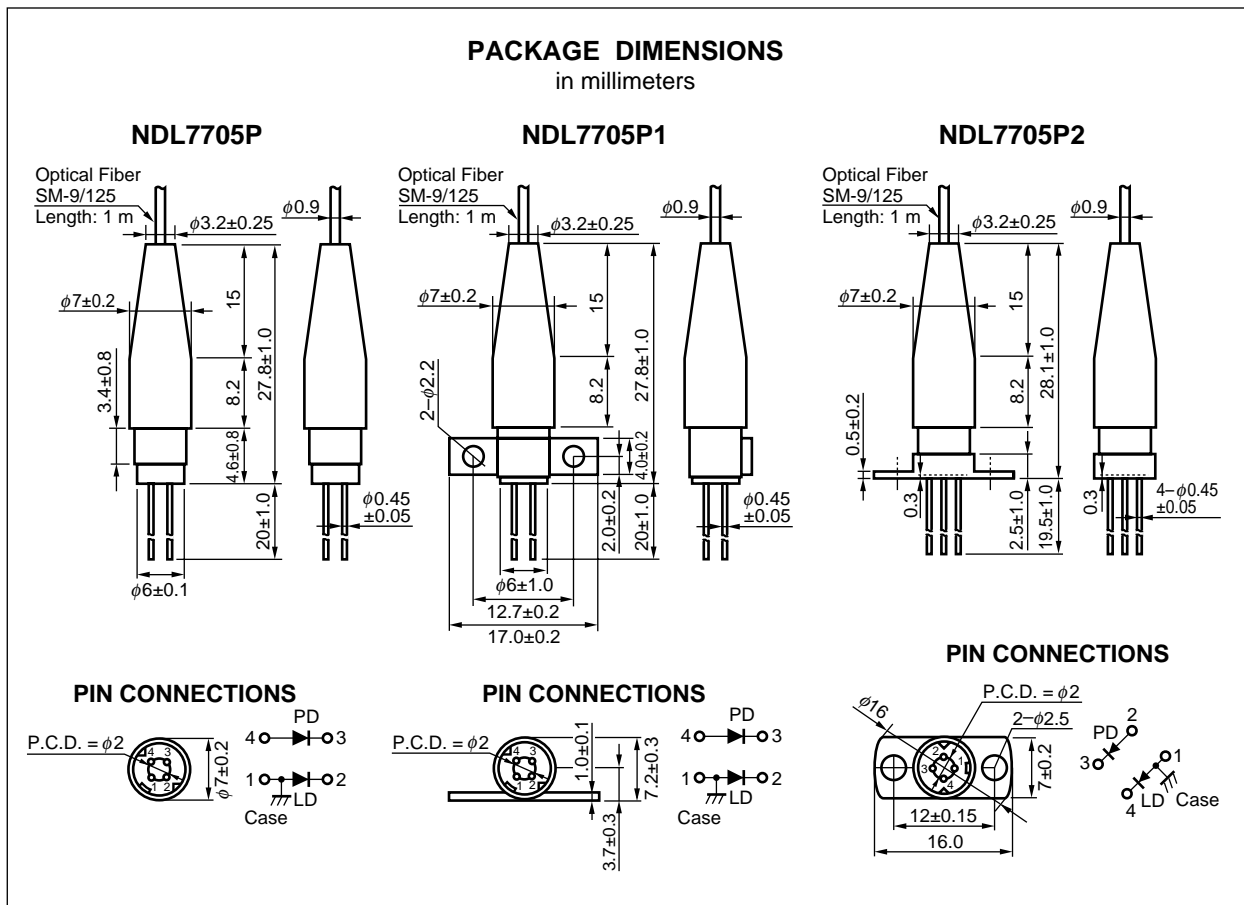
**DESCRIPTION**

The NDL7705P Series is a 1 550 nm phase-shifted DFB (Distributed Feed-Back) laser diode module with optical isolator. Multiple Quantum Well (MQW) structure is adopted to achieve stable dynamic single longitudinal mode operation over wide temperature range of  $-40$  to  $+85$  °C.

It is designed for all STM-1 and STM-4 applications.

**FEATURES**

- Peak emission wavelength  $\lambda_p = 1\ 550$  nm
- Optical output power  $P_f = 2.0$  mW
- Wide operating temperature range  $T_c = -40$  to  $+85$  °C
- $\lambda/4$ -phase-shifted DFB
- InGaAs monitor PIN-PD
- Internal optical isolator



The information in this document is subject to change without notice.

**ORDERING INFORMATION**

Part Number	Available Connector	Flange Type
NDL7705P	Without Connector	No flange
NDL7705PC	With FC-PC Connector	
NDL7705PD	With SC-PC Connector	
NDL7705P1	Without Connector	Flat Mount Flange
NDL7705P1C	With FC-PC Connector	
NDL7705P1D	With SC-PC Connector	
NDL7705P2	Without Connector	Vertical Mount Flange
NDL7705P2C	With FC-PC Connector	
NDL7705P2D	With SC-PC Connector	

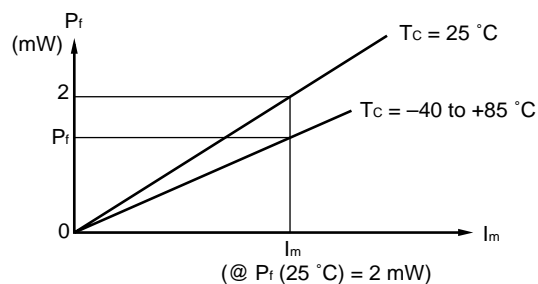
**ABSOLUTE MAXIMUM RATINGS (T<sub>c</sub> = 25 °C, unless otherwise specified)**

Parameter	Symbol	Ratings	Unit
Optical Output Power	P <sub>r</sub>	5.0	mW
Forward Current of LD	I <sub>F</sub>	I <sub>th</sub> +50	mA
Reverse Voltage of LD	V <sub>R</sub>	2.0	V
Forward Current of PD	I <sub>F</sub>	2.0	mA
Reverse Voltage of PD	V <sub>R</sub>	15	V
Operating Case Temperature	T <sub>c</sub>	-40 to +85	°C
Storage Temperature	T <sub>stg</sub>	-40 to +85	°C
Lead Soldering Temperature (10 s)	T <sub>slid</sub>	260	°C

**ELECTRO-OPTICAL CHARACTERISTICS (T<sub>c</sub> = -40 to +85 °C, unless otherwise specified)**

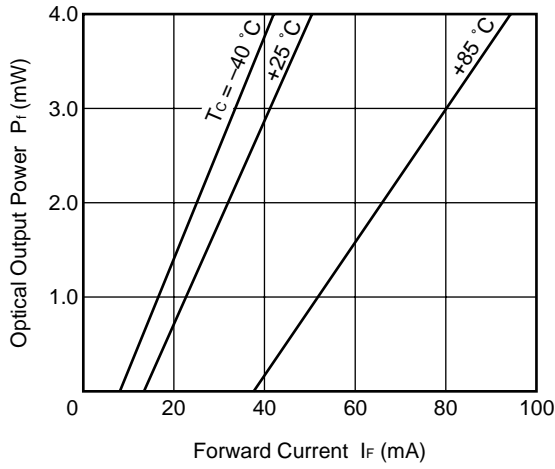
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 30 mA	0.9		1.3	V
Threshold Current	I <sub>th</sub>	T <sub>c</sub> = 25 °C		15		mA
		T <sub>c</sub> = 85 °C		35	50	
Differential Efficiency form Fiber	η <sub>d</sub>	T <sub>c</sub> = 25 °C	0.070	0.120		W/A
		T <sub>c</sub> = 85 °C	0.035	0.075		
Temperature Dependence of Differential Efficiency from Fiber	Δη <sub>d</sub>	Δη <sub>d</sub> = 10 log $\frac{\eta_d(85\text{ °C})}{\eta_d(25\text{ °C})}$	-3	-2		dB
Peak Emission Wavelength	λ <sub>p</sub>	P <sub>f</sub> = 1 mW	1 530	1 550	1 570	nm
Side Mode Suppression Ratio	SMSR	P <sub>f</sub> = 1 mW	30			dB
Rise Time	t <sub>r</sub>	I <sub>b</sub> = 0.9 × I <sub>th</sub>			0.5	ns
Fall Time	t <sub>f</sub>	I <sub>b</sub> = 0.9 × I <sub>th</sub>			0.5	ns
Monitor Current	I <sub>m</sub>	V <sub>R</sub> = 5 V, P <sub>f</sub> = 2 mW	300		2 500	μA
Monitor Dark Current	I <sub>D</sub>	V <sub>R</sub> = 5 V, T <sub>c</sub> = 25 °C		0.1	5	nA
Tracking Error	γ <sup>-1</sup>	I <sub>m</sub> = const. (P <sub>f</sub> = 2 mW, T <sub>c</sub> = 25 °C)			1.0	dB
Relative Intensity Noise	RIN	Ref = -14 dB, P <sub>f</sub> = 1 mW		-140	-130	dB/Hz

$$*1 \gamma = \left| 10 \log \frac{P_f}{2.0 \text{ mW}} \right|$$

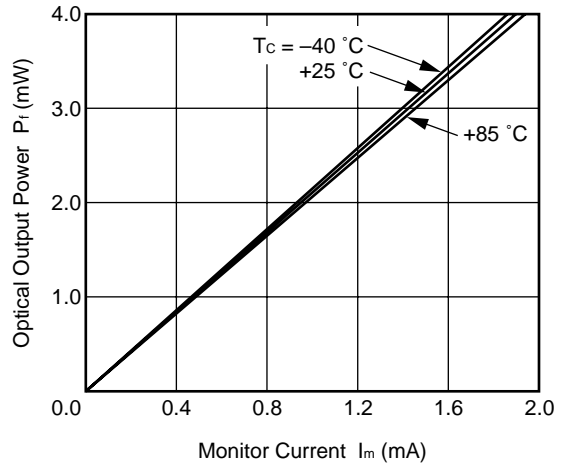


★ TYPICAL CHARACTERISTICS ( $T_c = 25\text{ }^\circ\text{C}$ , unless otherwise specified)

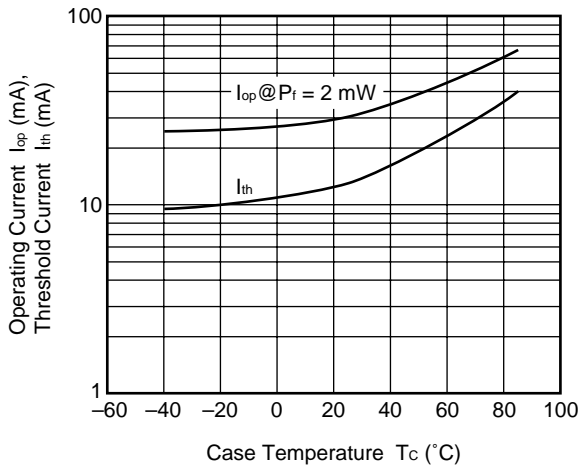
OPTICAL OUTPUT POWER vs. FORWARD CURRENT



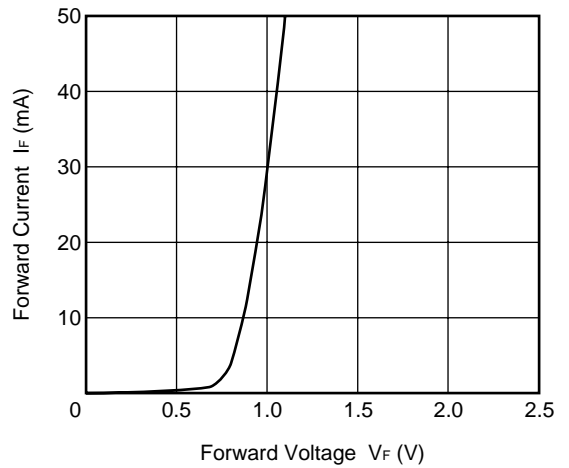
OPTICAL OUTPUT POWER vs. MONITOR CURRENT



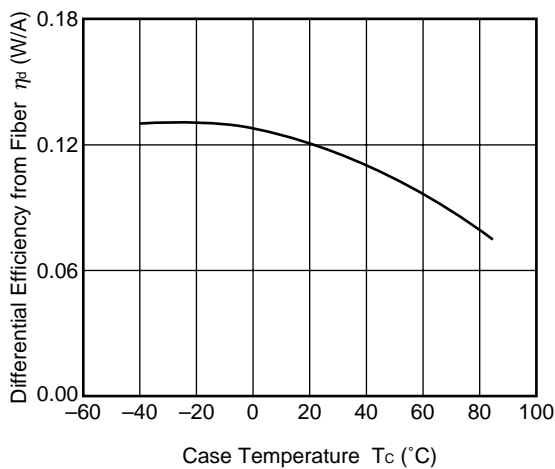
OPERATING CURRENT AND THRESHOLD CURRENT vs. CASE TEMPERATURE



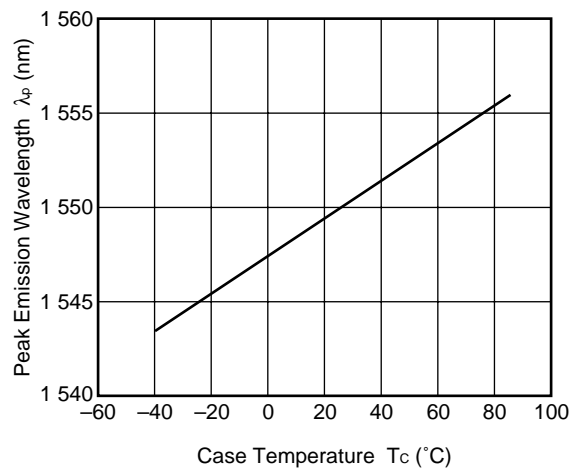
FORWARD CURRENT vs. FORWARD VOLTAGE



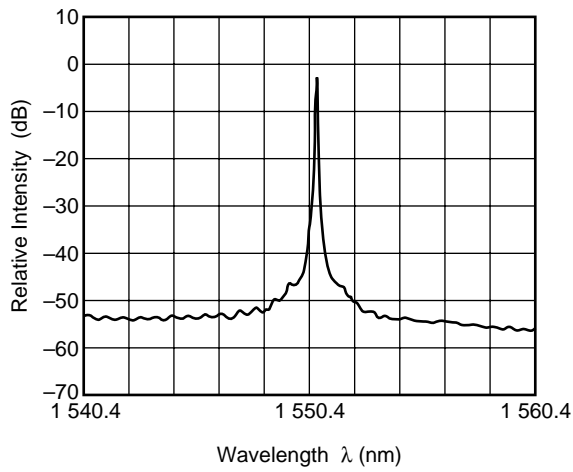
TEMPERATURE DEPENDENCE OF DIFFERENTIAL EFFICIENCY FROM FIBER



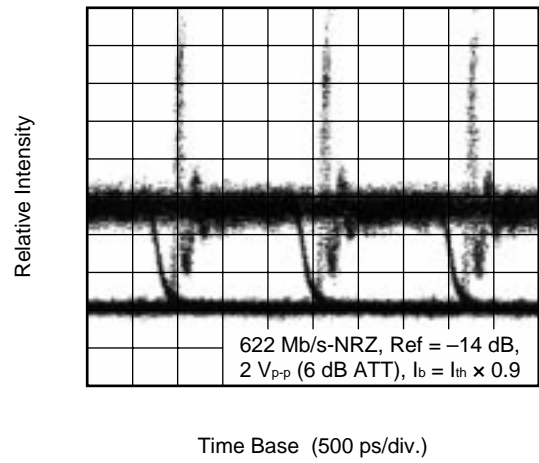
TEMPERATURE DEPENDENCE OF PEAK EMISSION WAVELENGTH



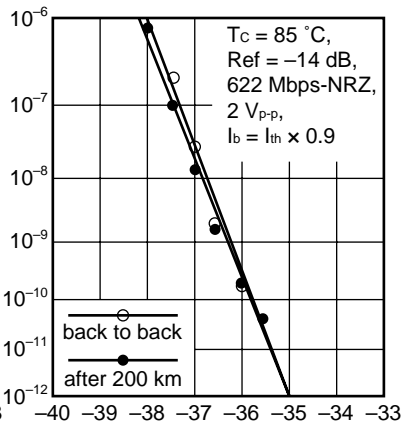
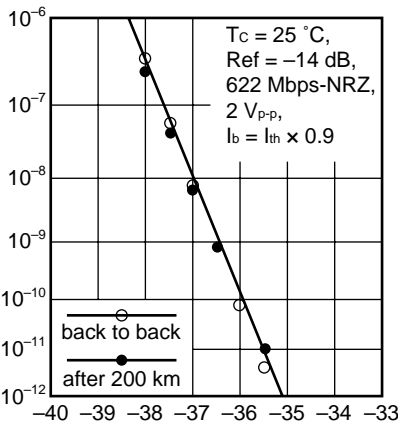
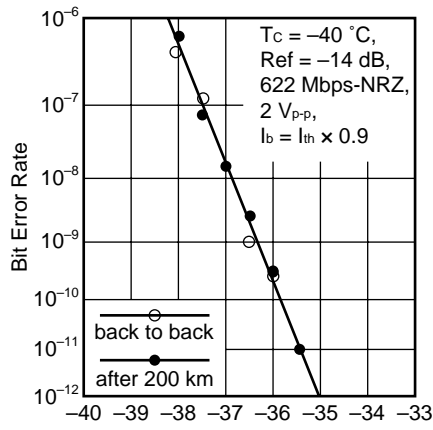
LONGITUDINAL MODE FROM FIBER



EYE DIAGRAM



ERROR RATE CHARACTERISTICS



Average Received Power  $\bar{P}$  (dBm)

★ **DFB-LD FAMILY FOR TELECOM**

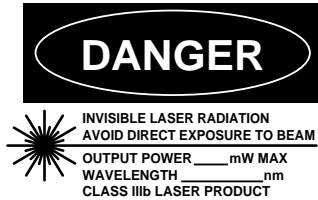
Part Number	Absolute Maximum Ratings		Typical Characteristics			SDH Application	Package
	T <sub>c</sub> (°C)	T <sub>stg</sub> (°C)	I <sub>th</sub> (mA)	P <sub>r</sub> (mW)	λ <sub>c</sub> (nm)		
			TYP.	MIN.	TYP.		
NDL7603P Series	-40 to +85	-40 to +85	15	2	1 310	≤ STM-4 : 622 Mb/s	Coaxial
NDL7620P Series	0 to +70	-40 to +85	45 (MAX.)	2	1 310	≤ STM-16: 2.5 Gb/s	Coaxial
NDL7701P Series	-20 to +85	-40 to +85	20	2	1 550	≤ STM-4 : 622 Mb/s	Coaxial
NDL7705P Series	-40 to +85	-40 to +85	15	2	1 550	≤ STM-4 : 622 Mb/s	Coaxial
NDL7740PA	-20 to +65	-40 to +85	40	20 (TYP.)	1 550	≤ STM-16: 2.5 Gb/s CW Light Source for external modulator	BFY
NDL7910P	-20 to +65	-40 to +70	7	3 (TYP.)	1 550	≤ STM-16: 2.5 Gb/s EA modulator integrate DFB-LD	BFY

**REFERENCE**

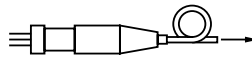
Document Name	Document No.
NEC semiconductor device reliability/quality control system	C11159E
Quality grades on NEC semiconductor devices	C11531E
Semiconductor device mounting technology manual	C10535E
Guide to quality assurance for semiconductor devices	MEI-1202
Semiconductor selection guide	X10679E

**CAUTION**

**Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. Please do not under any circumstances break the hermetic seal.**



**SEMICONDUCTOR LASER**



**AVOID EXPOSURE-Invisible Laser Radiation is emitted from this aperture**

**NEC Corporation**

NEC Building, 7-1, Shiba 5-chome, Minato-ku, Tokyo 108-01, Japan

Type number: \_\_\_\_\_

Manufactured: \_\_\_\_\_

Serial Number: \_\_\_\_\_

This product conforms to FDA regulations as applicable to standards 21 CFR Chapter 1, Subchapter J.

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**Special:** Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)

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Anti-radioactive design is not implemented in this product.